General Description

The SJH013N04 uses SGT technology to provide excellent $R_{DS(ON)}$, low gate charge and fast switching characteristics. This device is suitable for use as a wide variety of applications.

Features

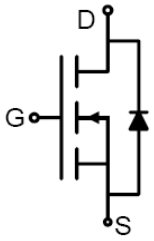
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

Application

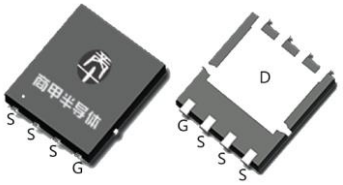
- DC/DC Converter
- Load Switching, Quick/Wireless Charging, Motor Driving

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(ON)\_TYP}$	1.2	mΩ
I_D	198	A
Q_G	101	nC



Schematic Diagram



PDFN5X6-8L top&bottom view

RoHS

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJH013N04	SJH013N04	PDFN5X6	Tape	\	\	5000 Pcs

Table 1. Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	40	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
I_D	Drain Current-Continuous(T_C=25℃)	198	A
	Drain Current-Continuous(T_C=100℃)	125	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	792	A
P_D	Maximum Power Dissipation(T_C=25℃)	96	W
	Maximum Power Dissipation(T_C=100℃)	38	W
E_{AS}	Avalanche energy (Note 2)	812	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.3	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	40			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=40V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=40V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	2		4	V
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D=20A		42		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=20A T_J=25℃		1.2	1.5	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=20V,V_{GS}=0V, f=1.0MHz		6112		pF
C_{oss}	Output Capacitance			2137		pF
C_{rss}	Reverse Transfer Capacitance			130		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		1.8		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V, V_{DS}=20V, R_L=1Ω, R_{GEN}=3Ω		25		nS
t_r	Turn-on Rise Time			20		nS
$t_{d(off)}$	Turn-Off Delay Time			55		nS
t_f	Turn-Off Fall Time			15		nS
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=20V, I_D=20A		101		nC
Q_{gs}	Gate-Source Charge			16		nC
Q_{gd}	Gate-Drain Charge			17.2		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				198	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=20A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=20A, dI/dt=100A/μs		75		ns
Q_{rr}	Reverse Recovery Charge	I_F=20A, dI/dt=100A/μs		125		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=30V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

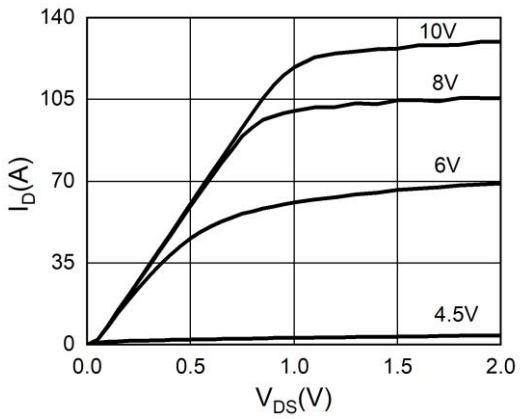


Figure 2. Transfer Characteristics

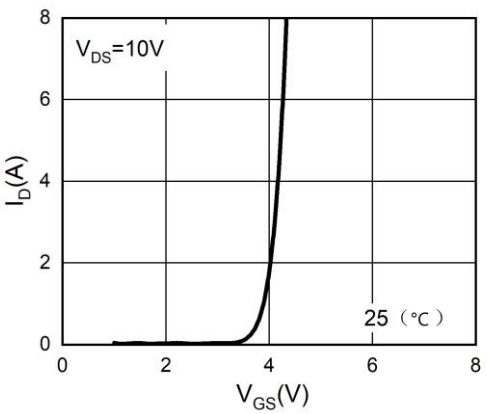


Figure 3. Power Dissipation

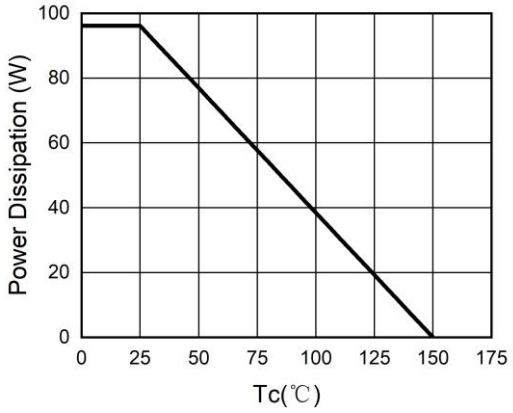


Figure 4. Drain Current

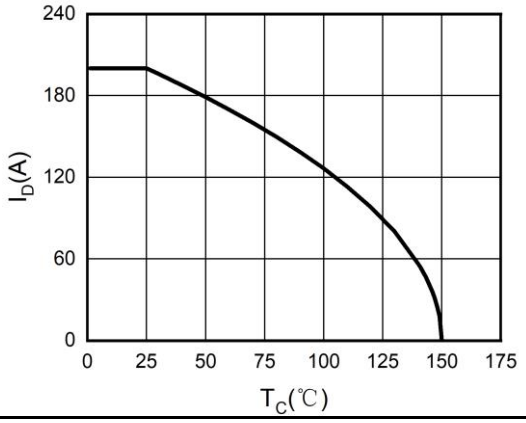


Figure 5. BV_{DSS} vs Junction Temperature

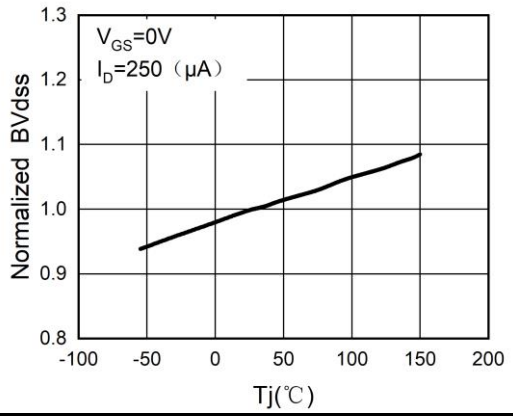
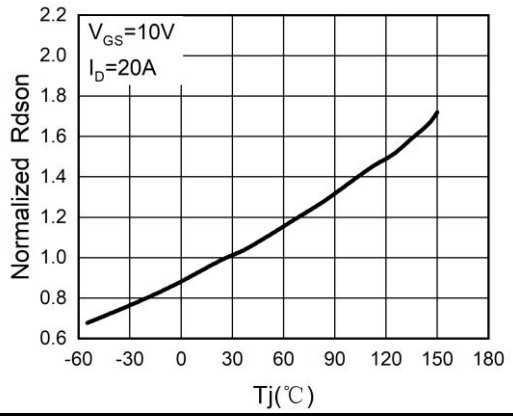


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

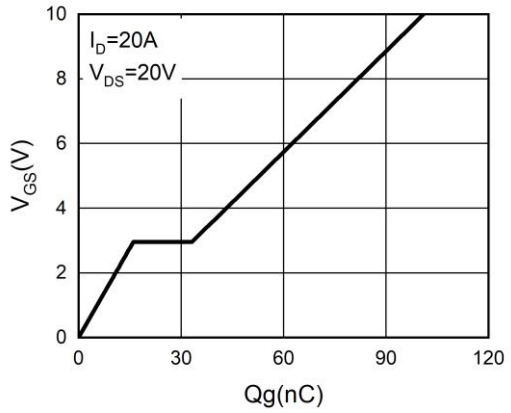


Figure 8. Capacitance

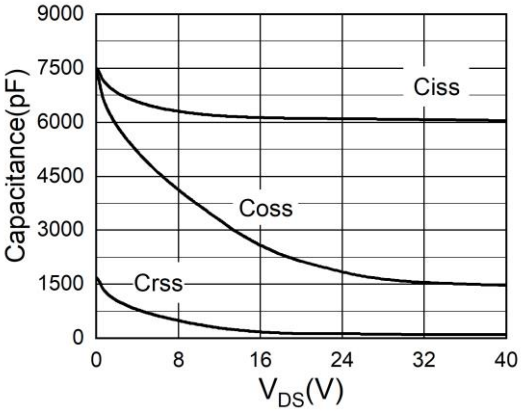


Figure 9. Body-Diode Characteristics

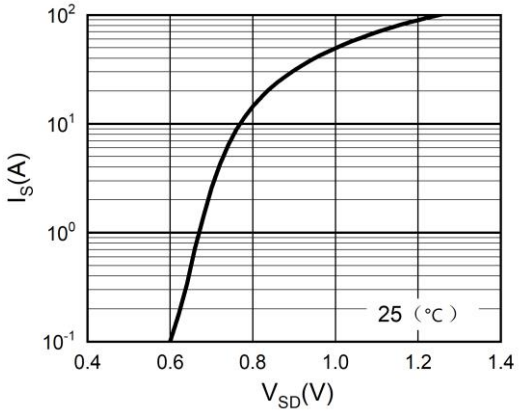
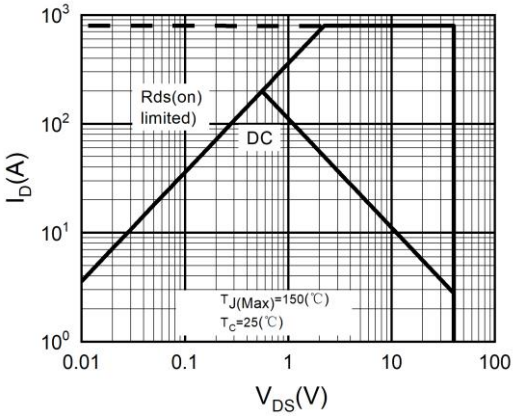
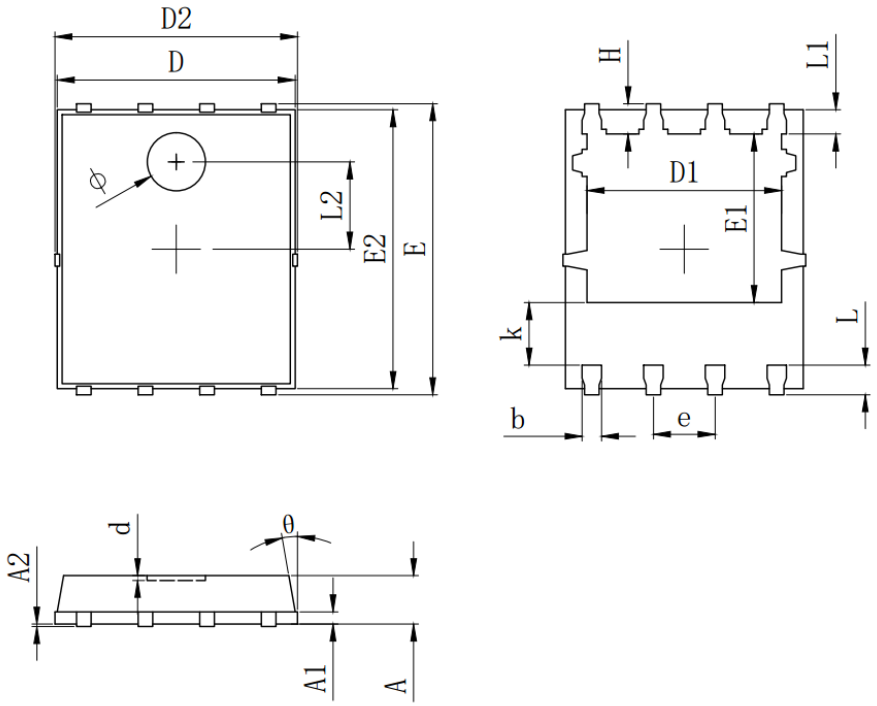


Figure 10. Maximum Safe Operating Area



PDFN5X6-8L Package Information



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100

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H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100

Attention

This product described in this document can not be used in life support devices or systems, aircraft's control systems, and other applications whose failure can be reasonably expected to result in serious physical and/or material damage，apart from that when an application agreement is signed between customer and Wuxi Shangjia Semiconductor

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